

FDM3622

N-Channel PowerTrench® MOSFET

100V, 4.4A, 60mΩ

Features

- Max $r_{DS(on)}$ = 60mΩ at $V_{GS} = 10V$, $I_D = 4.4A$
- Max $r_{DS(on)}$ = 80mΩ at $V_{GS} = 6.0V$, $I_D = 3.8A$
- Low Miller Charge
- Low QRR Body Diode
- Optimized efficiency at high frequencies
- UIS Capability (Single Pulse and Repetitive Pulse)
- RoHS Compliant

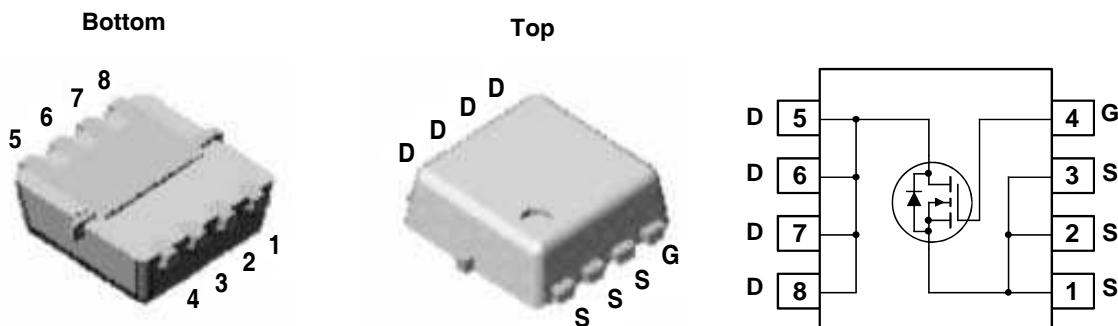


General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

Application

- Distributed Power Architectures and VRMs.
- Primary Switch for 24V and 48V Systems
- High Voltage Synchronous Rectifier
- Formerly developmental type 82744



Power 33

MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	100	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current -Continuous	4.4	A
	-Pulsed	20	
P_D	Power Dissipation	2.1	W
	Power Dissipation	0.9	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	3.0	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	60	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDM3622	FDM3622	Power 33	7"	8mm	3000 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	100			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{V}$, $V_{GS} = 0\text{V}$ $T_J = 100^\circ\text{C}$			1 250	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	2		4	V
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 4.4\text{A}$		44	60	$\text{m}\Omega$
		$V_{GS} = 6.0\text{V}$, $I_D = 3.8\text{A}$		56	80	
		$V_{GS} = 10\text{V}$, $I_D = 4.4\text{A}$, $T_J = 150^\circ\text{C}$		92	120	

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		820	1090	pF
C_{oss}	Output Capacitance			125	170	pF
C_{rss}	Reverse Transfer Capacitance			35	55	pF
R_g	Gate Resistance	$V_{DS} = 15\text{mV}$, $f = 1\text{MHz}$		3.1		Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\text{V}$, $I_D = 4.4\text{A}$ $V_{GS} = 10\text{V}$, $R_{GEN} = 24\Omega$		11	20	ns
t_r	Rise Time			25	40	ns
$t_{d(off)}$	Turn-Off Delay Time			35	56	ns
t_f	Fall Time			26	42	ns
Q_g	Total Gate Charge	$V_{GS} = 10\text{V}$		13	17	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DD} = 50\text{V}$		3.6		nC
Q_{gd}	Gate to Drain "Miller" Charge	$I_D = 4.4\text{A}$		3.4		nC

Drain-Source Diode Characteristics

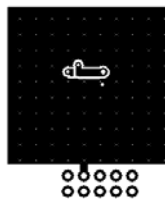
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = 4.4\text{A}$			1.25	V
		$V_{GS} = 0\text{V}$, $I_S = 2.2\text{A}$			1.0	V
t_{rr}	Reverse Recovery Time	$I_F = 4.4\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$			56	ns
Q_{rr}	Reverse Recovery Charge				108	nC

Notes:

1: $R_{\theta JA}$ is determined with the device mounted on a 1 in² oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.

(a) $R_{\theta JA} = 60^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper, 1.5'x1.5'x0.062' thick PCB.

(b) $R_{\theta JA} = 135^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper.



a. $60^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper



b. $135^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

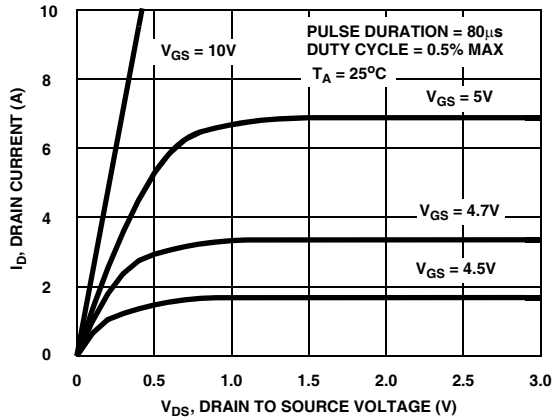


Figure 1. On-Region Characteristics

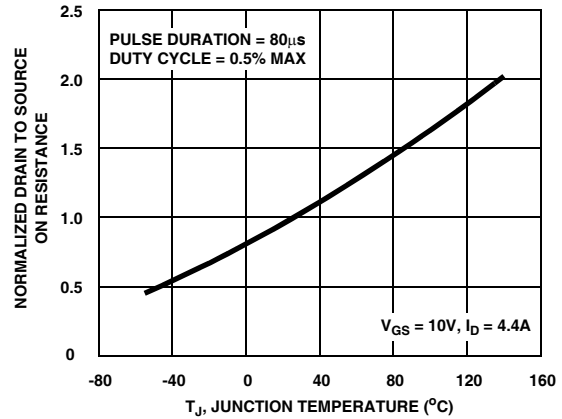


Figure 2. Normalized On-Resistance vs Junction Temperature

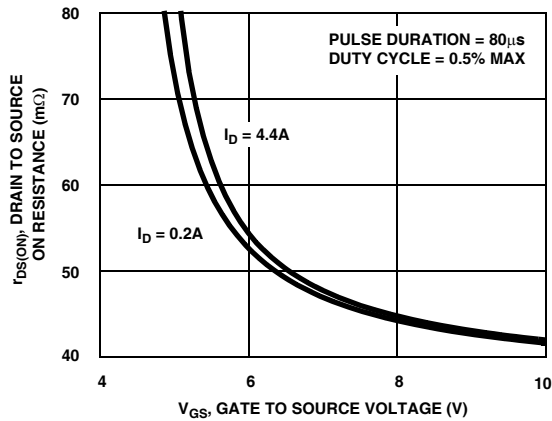


Figure 3. On-Resistance vs Gate to Source Voltage

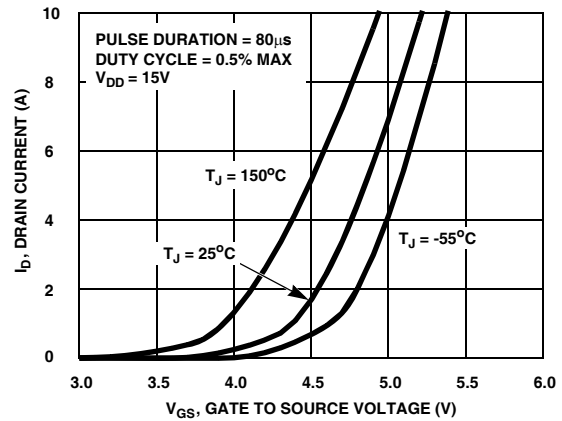


Figure 4. Transfer Characteristics

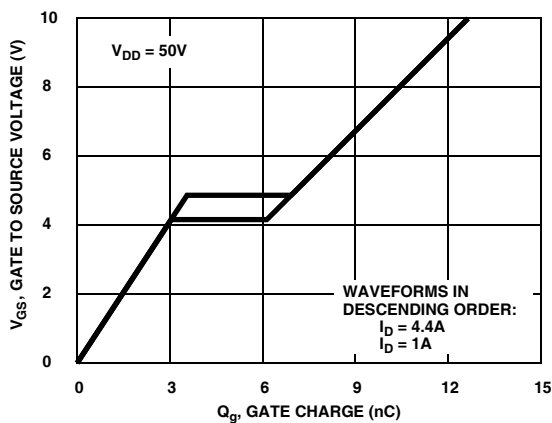


Figure 5. Gate Charge Characteristics

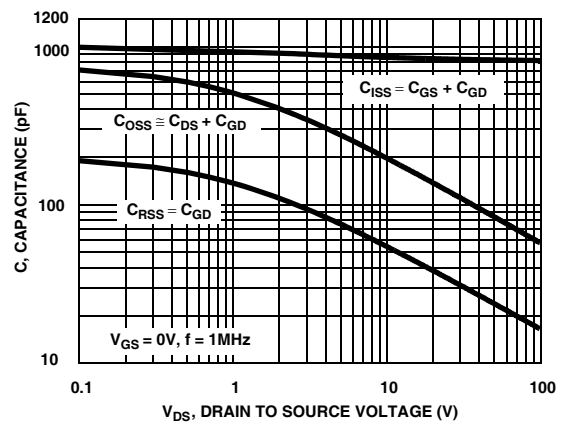


Figure 6. Capacitance vs Drain to Source Voltage

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

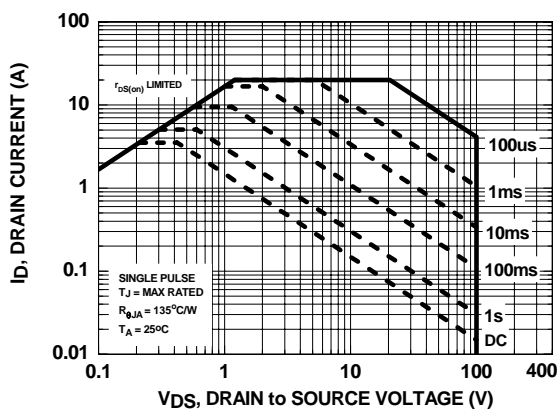


Figure 7. Forward Bias Safe Operating Area

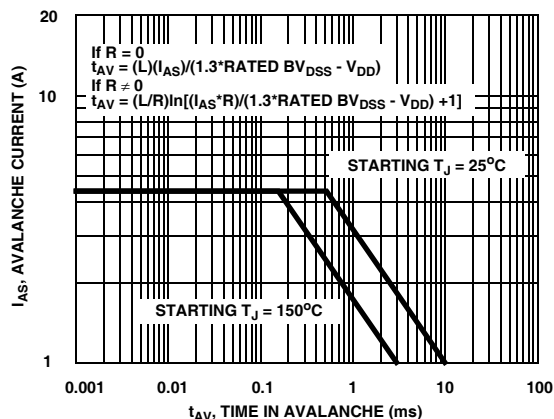


Figure 8. Unclassified Inductive Switching Capability

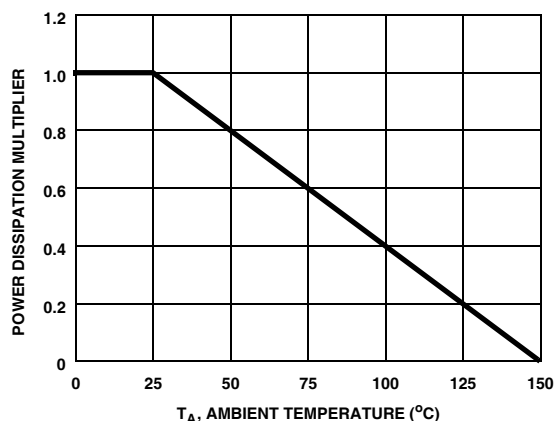


Figure 9. Normalized Power dissipation vs Ambient Temperature

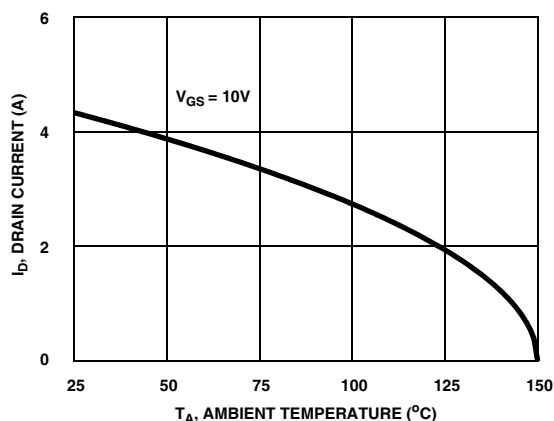


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

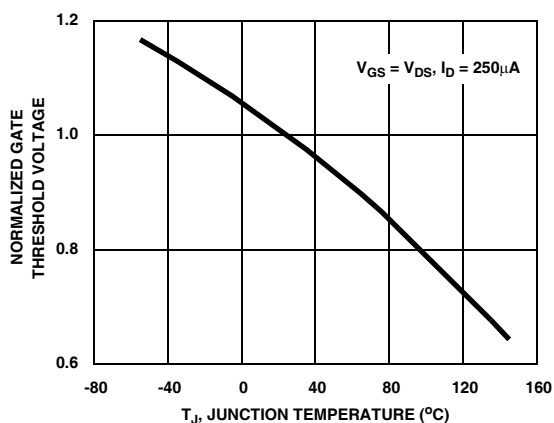


Figure 11. Normalized Gate Threshold voltage vs Junction Temperature

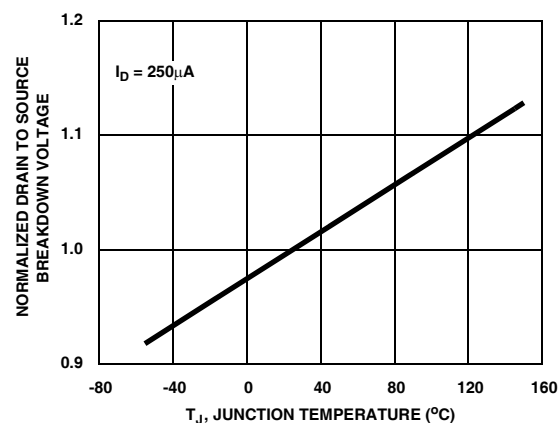


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

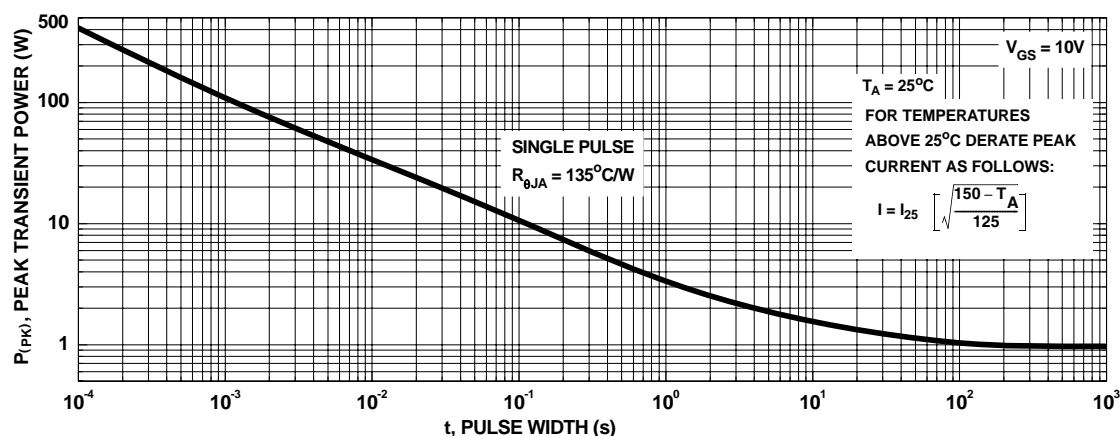


Figure 13. Peak Current Capability

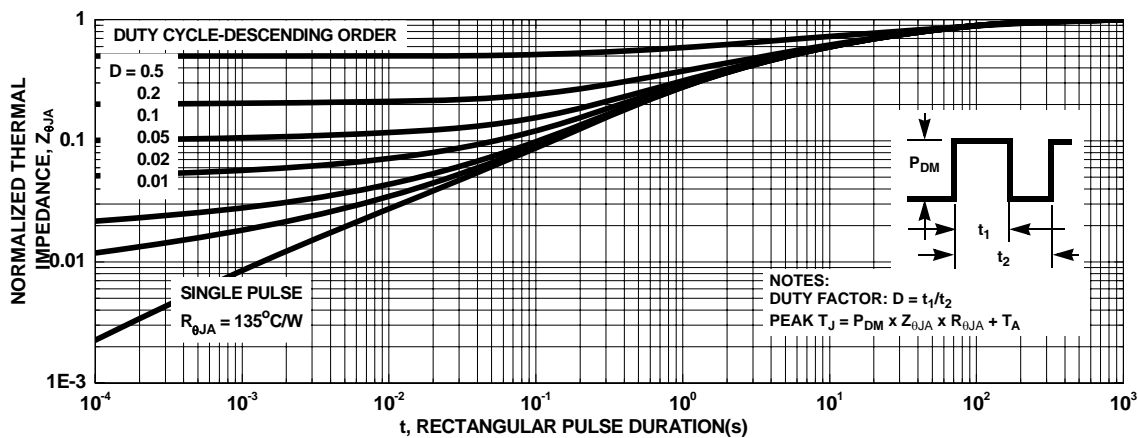
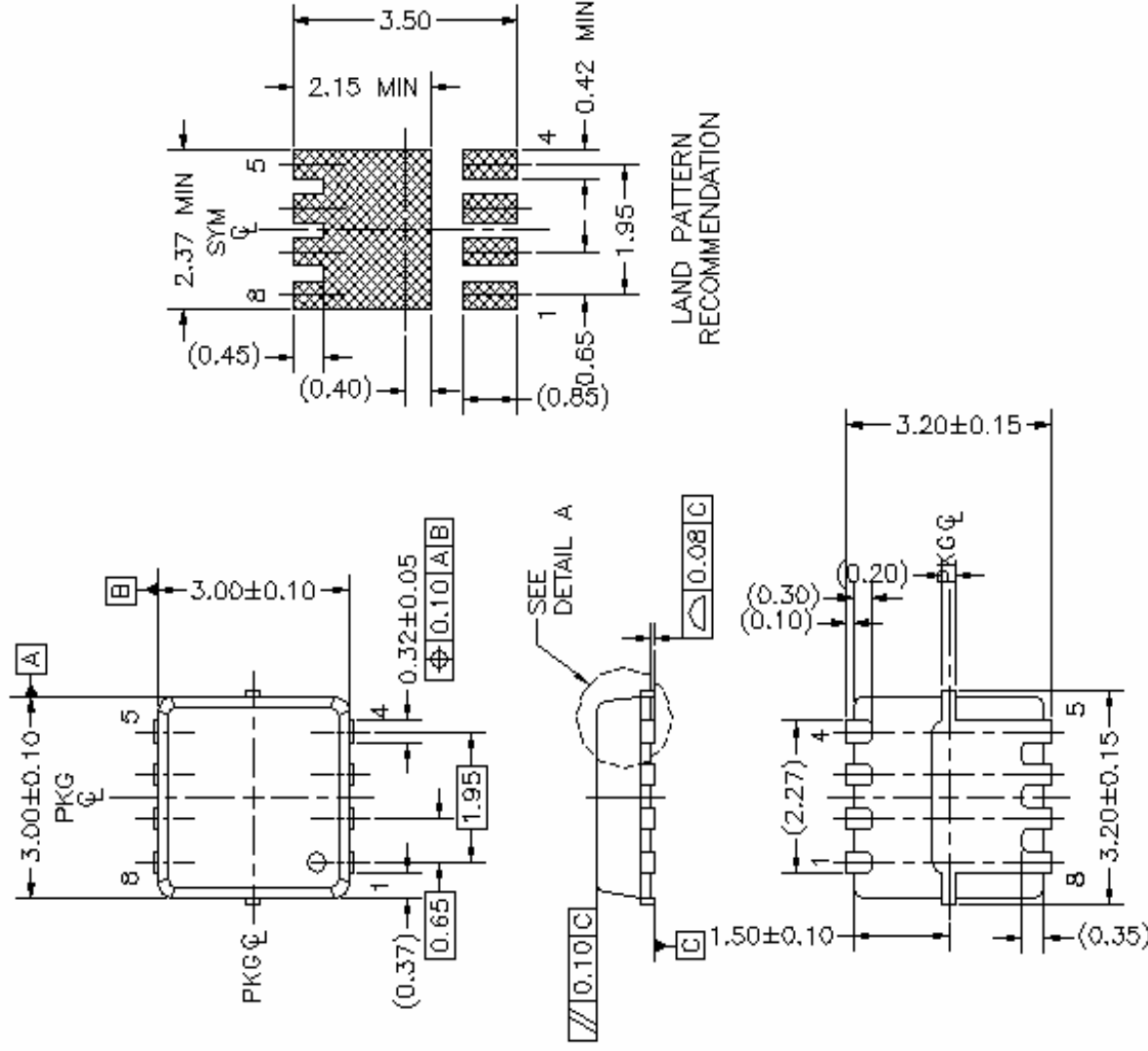


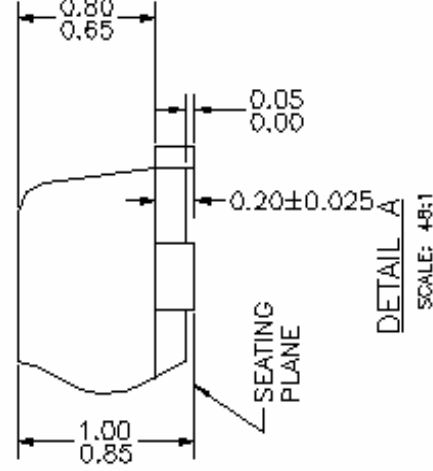
Figure 14. Transient Thermal Response Curve

FDM3622 N-Channel PowerTrench® MOSFET



NOTES: UNLESS OTHERWISE SPECIFIED

- A) NO PACKAGE STANDARD REFERENCE AS OF 29 JUNE 2002.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.



DETAIL A
SCALE: 4x:1

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FAST®	MicroFET™	QS™	TinyBuck™	
FASTr™	MicroPak™	QT Optoelectronics™	TinyPWM™	
FPS™	MICROWIRE™	Quiet Series™	TinyPower™	
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	MSXPro™	RapidConnect™	TINYOPTO™	
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Programmable Active Droop™				

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Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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